



OPA606

Wide-Bandwidth *Difet* ® OPERATIONAL AMPLIFIER

FEATURES

WIDE BANDWIDTH: 13MHz typ
 HIGH SLEW RATE: 35V/μs typ

● LOW BIAS CURRENT: 10pA max at

 $T_A = +25^{\circ}C$

LOW OFFSET VOLTAGE: 500µV max
 LOW DISTORTION: 0.0035% typ at 10kHz

APPLICATIONS

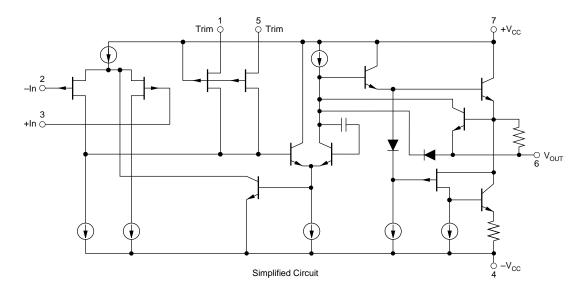
- OPTOELECTRONICS
- DATA ACQUISITION
- TEST EQUIPMENT
- AUDIO AMPLIFIERS

DESCRIPTION

The OPA606 is a wide-bandwidth monolithic dielectrically-isolated FET (*Difet*®) operational amplifier featuring a wider bandwidth and lower bias current than BIFET® LF156A amplifiers. Bias current is specified under warmed-up and operating conditions, as opposed to a junction temperature of +25°C.

Laser-trimmed thin-film resistors offer improved offset voltage and noise performance.

The OPA606 is internally compensated for unity-gain stability.



Difet®; Burr-Brown Corp.

BIFET®; National Semiconductor Corp.

International Airport Industrial Park

• Mailing Address: PO Box 11400

• Tucson, AZ 85734

• Street Address: 6730 S. Tucson Blvd.

• Tucson, AZ 85706

Tel: (520) 746-1111

• Twx: 910-952-1111

• Cable: BBRCORP

• Telex: 066-6491

• FAX: (520) 889-1510

• Immediate Product Info: (800) 548-6132

SPECIFICATIONS

ELECTRICAL

At V $_{\rm CC}$ = $\pm 15 VDC$ and T $_{\rm A}$ = +25 $^{\circ}C$ unless otherwise noted.

			OPA606KI	И	OPA606LM		OPA606KP				
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
FREQUENCY RESPONSE											
Gain Bandwidth	Small Signal	10	12.5		11	13		9	12		MHz
Full Power Response	20Vp-p, $R_L = 2kΩ$		515			550			470		kHz
Slew Rate	$V_0 = \pm 10V$,	22	33		25	35		20	30		V/μs
	$R_L = 2k\Omega$										
Settling Time(1): 0.1%	Gain = −1,		1.0			1.0			1.0		μs
	$R_L = 2k\Omega$										·
0.01%	10V Step		2.1			2.1			2.1		μs
Total Harmonic Distortion	G = +1, 20Vp-p		0.0035			0.0035			0.0035		%
	$R_L = 2k\Omega$										
	f = 10kHz										
INPUT OFFSET VOLTAGE(2)											
Input Offset Voltage	V _{CM} = 0VDC		±180	±1.5mV		±100	±500		±300	±3mV	μV
Average Drift	$T_A = T_{MIN}$ to T_{MAX}		±5			±3	±5		±10		μV/°C
Supply Rejection	$V_{CC} = \pm 10V \text{ to } \pm 18V$	82	100		90	104		80	90		dB
			±10	±79		±6	±32		±32	±100	μV/V
BIAS CURRENT(2)											
Input Bias Current	$V_{CM} = 0VDC$		±7	±15		±5	±10		±8	±25	pA
OFFSET CURRENT(2)											
Input Offset Current	$V_{CM} = 0VDC$		±0.6	±10		±0.4	±5		±1	±15	pA
NOISE											
Voltage, f _O = 10Hz	100% tested (L)		37			30	40		37		nV/√Hz
100Hz	100% tested (L)		21			20	28		21		nV/√Hz
1kHz	100% tested (L)		14			13	16		14		nV/√ <u>Hz</u>
10kHz	(3)		12			11	13		12		nV/√ <u>Hz</u>
20kHz	(3)		11			10.5	13		11		nV/√Hz
$f_B = 10Hz$ to $10kHz$	(3)		1.3			1.2	1.5		1.3		μVr <u>ms</u>
Current, $f_0 = 0.1Hz$ thru 20kHz	; ; (3)		1.5			1.3	2		1.7		fA/√Hz
IMPEDANCE											
Differential			10 ¹³ 1			1013 1			10 ¹³ 1		$\Omega \parallel pF$
Common-Mode			1014 3			1014 3			1014 3		$\Omega \parallel pF$
VOLTAGE RANGE											
Common-Mode Input Range		±10.5	±11.5		±11	±11.6		±10.2	±11		V
Common-Mode Rejection	$V_{IN} = \pm 10 VDC$	80	95		85	96		78	90		dB
OPEN-LOOP GAIN, DC											
Open-Loop Voltage Gain	$R_L \ge 2k\Omega$	95	115		100	118		90	110		dB
RATED OUTPUT											
Voltage Output	$R_L = 2k\Omega$	±11	±12.2		±12	±12.6		±11	±12		V
Current Output	$V_O = \pm 10 VDC$	±5	±10		±5	±10		±5	±10		mA
Output Resistance	DC, Open Loop		40			40			40		Ω
Load Capacitance Stability	Gain = +1		1000			1000			1000		pF
Short Circuit Current		10	20		10	20		10	20		mA
POWER SUPPLY											
Rated Voltage			±15			±15			±15		VDC
Voltage Range,											
Derated Performance		±5		±18	±5		±18	±5		±18	VDC
Current, Quiescent	$I_O = 0mADC$		6.5	9.5		6.2	9		6.5	10	mA
TEMPERATURE RANGE											
Specification	Ambient Temperature										
_	KM, KP, LM	0		+70	0		+70	0		+70	°C
Operating	Ambient Temperature	- 55		+125	-55		+125	-40		+85	°C
$ heta_{\sf JA}$			200			200		1	155		°C/W

NOTES: (1) See settling time test circuit in Figure 2. (2) Offset voltage, offset current, and bias current are measured with the units fully warmed up. (3) Sample tested—this parameter is guaranteed on L grade only.



ELECTRICAL (FULL TEMPERATURE RANGE SPECIFICATIONS)

At V_{CC} = ±15VDC and T_A = T_{MIN} to T_{MAX} unless otherwise noted.

		(OPA606KM OPA606LM		OPA606KP						
PARAMETER	CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
TEMPERATURE RANGE Specification Range	Ambient Temp.	0		+70	0		+70	0		+70	°C
INPUT OFFSET VOLTAGE ⁽¹⁾	Ambient Temp.	0		+70	0		+70	0		+70	- 0
Input Offset Voltage Average Drift	V _{CM} = 0VDC		±400 ±5	±2mV		±335 ±3	±750 ±5		±750 ±10	±3.5mV	μV μV/°C
Supply Rejection	$V_{CC} = \pm 10V \text{ to } \pm 18V$	80	98 ±13	±100	85	100 ±10	±56	78	95 ±18	±126	dΒ μV/V
BIAS CURRENT ⁽¹⁾ Input Bias Current	V _{CM} = 0VDC		±158	±339		±113	±226		±181	±566	pA
OFFSET CURRENT ⁽¹⁾ Input Offset Current	V _{CM} = 0VDC		±14	±226		±9	±113		±23	±339	pA
VOLTAGE RANGE Common-Mode Input Range Common-Mode Rejection	V _{IN} = ±10VDC	±10.4 78	±11.4 92		±10.9 82	±11.5 95		±10 75	±10.9 88		V dB
OPEN-LOOP GAIN, DC Open-Loop Voltage Gain	$R_L \ge 2k\Omega$	90	106		95	112		88	104		dB
RATED OUTPUT Voltage Output Current Output	$R_{L} = 2k\Omega$ $V_{O} = \pm 10VDC$	±10.5 ±5	±12 ±10		±11.5 ±5	±12.4 ±10		±10.4 ±5	±11.8 ±10		V mA
POWER SUPPLY Current, Quiescent	I _O = 0mADC		6.6	10		6.4	9.5		6.6	10.5	mA

NOTES: (1) Offset voltage, offset current, and bias current are measured with the units fully warmed up.

ABSOLUTE MAXIMUM RATINGS

Supply Voltage(1)	
Internal Power Dissipation (1)	
Differential Input Voltage	±36VDC
Input Voltage Range	±18VDC
Storage Temperature Range	$M = -65^{\circ}C$ to $+150^{\circ}C$
	$P = -40^{\circ}C$ to $+85^{\circ}C$
Operating Temperature Range	$M = -55^{\circ}C$ to $+125^{\circ}C$
	$P = -40^{\circ}C$ to $+85^{\circ}C$
Lead Temperature (soldering, 10s)	+300°C
Output Short-Circuit Duration(3)	Continuous
Junction Temperature	+175°C

NOTES: (1) Packages must be derated based on θ_{JC} = 15°C/W or $\theta_{JA}.$ (2) For supply voltages less than ± 18 VDC, the absolute maximum input voltage is equal to the negative supply voltage. (3) Short circuit may be to power supply common only. Rating applies to +25°C ambient. Observe dissipation limit and $T_{\rm J}.$

PACKAGE INFORMATION

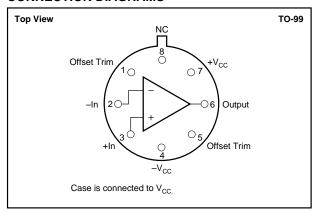
MODEL	PACKAGE	PACKAGE DRAWING NUMBER ⁽¹⁾
OPA606KM	TO-99	001
OPA606LM	TO-99	001
OPA606KP	Plastic DIP	006

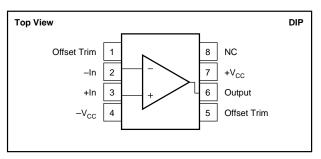
NOTE: (1) For detailed drawing and dimension table, please see end of data sheet, or Appendix D of Burr-Brown IC Data Book.

ORDERING INFORMATION

MODEL	PACKAGE	TEMPERATURE RANGE
OPA606KM	TO-99	0°C to 70°C
OPA606LM	TO-99	0°C to 70°C
OPA606KP	Plastic DIP	0°C to 70°C

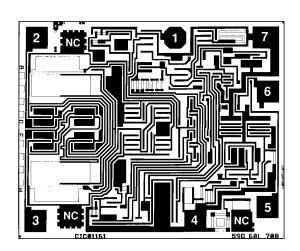
CONNECTION DIAGRAMS







DICE INFORMATION



	COC	DIE	TO	200	RAPI	VL
UPA	เทเมต	DIE	101	~()(3	RAPI	7 Y

FUNCTION			
Offset Trim			
–In			
+In			
-V _S			
Offset Trim			
Output			
+V _S			
NC			
No Connection			

Substrate Bias: No Connection.

MECHANICAL INFORMATION

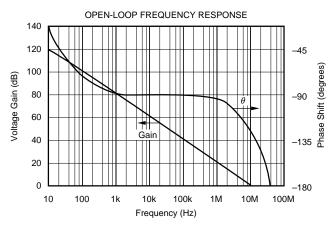
	MILS (0.001")	MILLIMETERS
Die Size Die Thickness Min. Pad Size	65 x 54 ±5 20 ±3 4 x 4	1.65 x 1.37 ±0.13 0.51 ±0.08 0.10 x 0.10
Backing Transistor Count		None 43

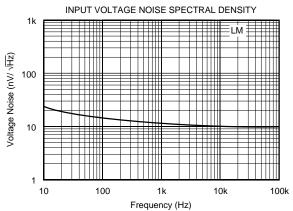
The information provided herein is believed to be reliable; however, BURR-BROWN assumes no responsibility for inaccuracies or omissions. BURR-BROWN assumes no responsibility for the use of this information, and all use of such information shall be entirely at the user's own risk. Prices and specifications are subject to change without notice. No patent rights or licenses to any of the circuits described herein are implied or granted to any third party. BURR-BROWN does not authorize or warrant any BURR-BROWN product for use in life support devices and/or systems.

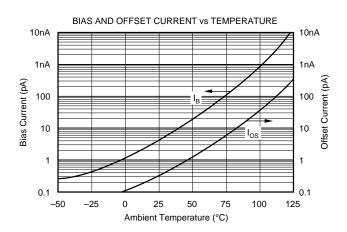


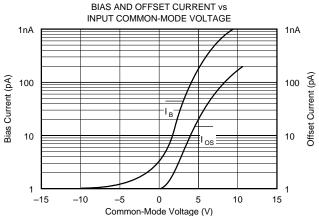
TYPICAL PERFORMANCE CURVES

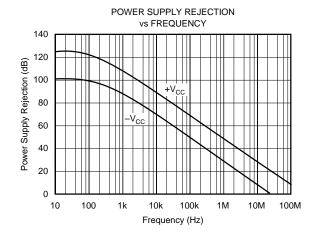
 $T_A = +25$ °C, $V_{CC} = \pm 15$ VDC unless otherwise noted.

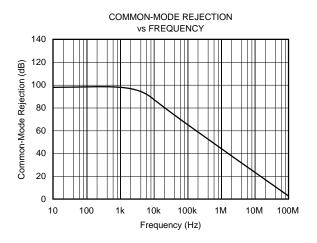






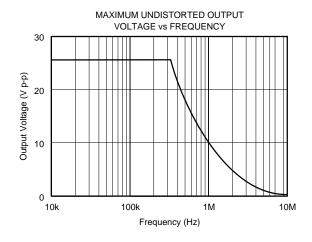


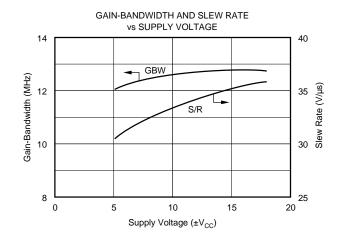


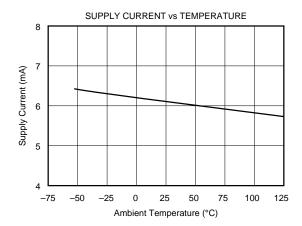


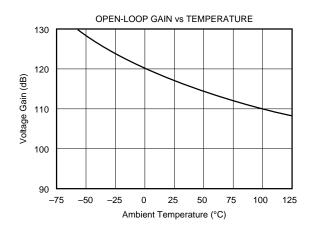
TYPICAL PERFORMANCE CURVES (CONT)

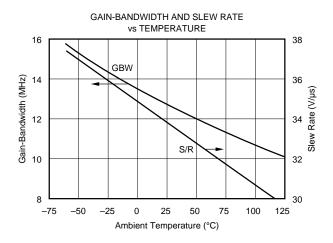
 T_A = +25°C, V_{CC} = ±15V unless otherwise noted.

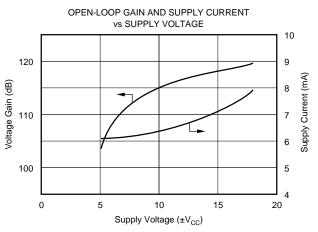








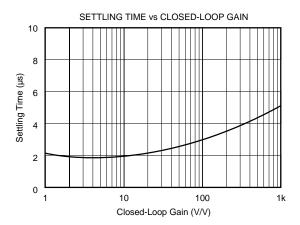


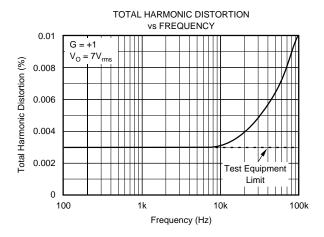


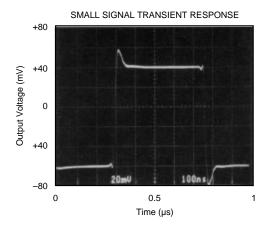


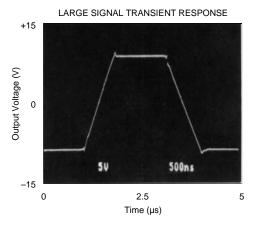
TYPICAL PERFORMANCE CURVES (CONT)

 $T_A = +25$ °C, $V_{CC} = \pm 15$ V unless otherwise noted.









APPLICATIONS INFORMATION

OFFSET VOLTAGE ADJUSTMENT

The OPA606 offset voltage is laser-trimmed and will require no further trim for most applications. As with most amplifiers, externally trimming the remaining offset can change drift performance by about $0.5\mu V/^{\circ}C$ for each millivolt of adjusted offset. Note that the trim (Figure 1) is similar to operational amplifiers such as LF156 and OP-16. The OPA606 can replace most other amplifiers by leaving the external null circuit unconnected.

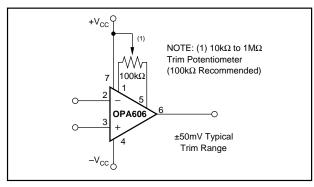


FIGURE 1. Offset Voltage Trim.

INPUT PROTECTION

Static damage can cause subtle changes in amplifier input characteristics without necessarily destroying the device. In precision operational amplifiers (both bipolar and FET types), this may cause a noticeable degradation of offset voltage and drift. Static protection is recommended when handling any precision IC operational amplifier.

If the input voltage exceeds the amplifier's negative supply voltage, input current limiting must be used to prevent damage.

CIRCUIT LAYOUT

Wideband amplifiers require good circuit layout techniques and adequate power supply bypassing. Short, direct connections and good high frequency bypass capacitors (ceramic or tantalum) will help avoid noise pickup or oscillation.

GUARDING AND SHIELDING

As in any situation where high impedances are involved, careful shielding is required to reduce "hum" pickup in input leads. If large feedback resistors are used, they should also be shielded along with the external input circuitry.

Leakage currents across printed circuit boards can easily exceed the bias current of the OPA606. To avoid leakage problems, it is recommended that the signal input lead of the OPA606 be wired to a Teflon® standoff. If the OPA606 is to be soldered directly into a printed circuit board, utmost care must be used in planning the board layout.

A "guard" pattern should completely surround the high impedance input leads and should be connected to a low impedance point which is at the signal input potential (see Figure 3).

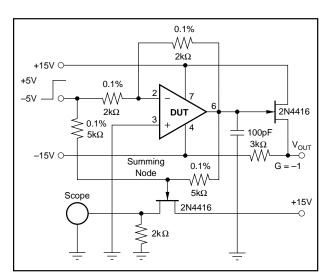


FIGURE 2. Settling Time Test Circuit.

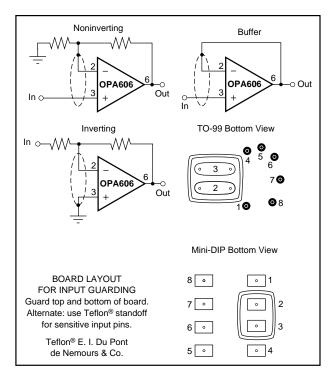


FIGURE 3. Connection of Input Guard.

APPLICATIONS CIRCUITS

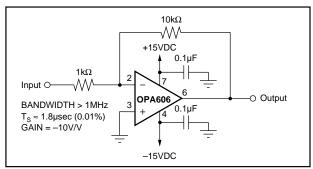


FIGURE 4. Inverting Amplifier.

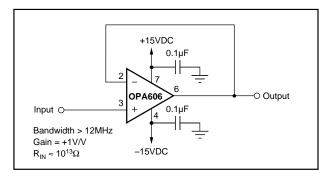


FIGURE 5. Noninverting Buffer.



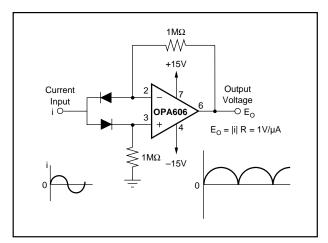


FIGURE 6. Absolute Value Current-to-Voltage Circuit.

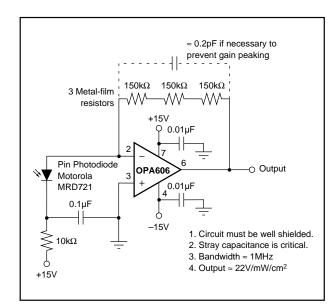


FIGURE 7. High-Speed Photodetector.

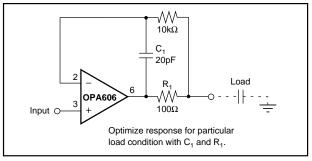


FIGURE 8. Isolating Load Capacitance from Buffer.

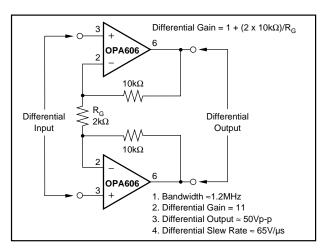


FIGURE 9. Differential Input/Differential Output Amplifier.

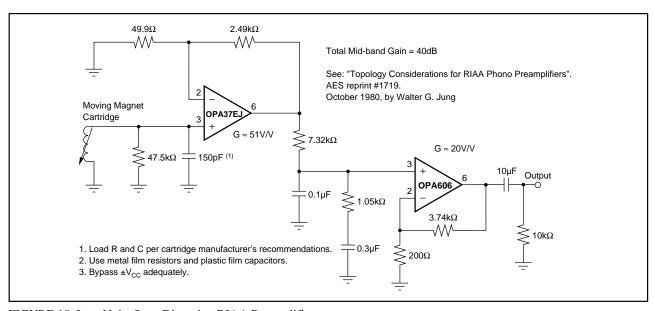


FIGURE 10. Low Noise/Low Distortion RIAA Preamplifier.



IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated